	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	23	"5608249"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:19			0
2	BRS	L8	14	"5940676"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:19			0
3	BRS	L15	11	"6239460"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:19			0
4	BRS	L22	24	"5699291"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:20			0
5	BRS	L29	9	"6165833"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:20			0
6	BRS	L36	10	"6251720"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:20			0
7	BRS	L43	8	"5783462"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:21			0
8	BRS	L50	6	"5869382"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:21			0
9	BRS	L57	99	1 or 8 or 15 or 22 or 29 or 36 or 43 or 50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:21			0
10	BRS	L71	57	57 and (barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:24			0
11	BRS	L78	46	71 and (((threshold adj1 voltage) or voltage or current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:23			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
12	BRS	L85	38	78 and ((silicon adj1 nitride) or ("Si.sub.3 N.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:26			0
13	BRS	L92	30	85 and (planar$6 or polish$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:27			0
14	BRS	L99	30	92 and (dielectric or (tantalum adj1 oxide) or ("Ta.sub.2 O.sub.5"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:28			0
15	BRS	L106	5	99 and ("N.sub.2 O")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:29			0
16	BRS	L113	30	99 and (anneal$5 or oxide or ("O.sub.2") or thermal or oxidation or heat or temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:30			0
17	BRS	L120	29	113 and (transistor or gate or source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 10:31			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Erro rs
1	BRS	L57	99	1 or 8 or 15 or 22 or 29 or 36 or 43 or 50	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:21			0
2	BRS	L71	57	57 and (barrier)	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:24			0
3	BRS	L78	46	71 and ((threshold adj1 voltage) or voltage or current)	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:23			0
4	BRS	L85	38	78 and ((silicon adj1 nitride) or ("Si.sub.3 N.sub.4"))	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:26			0
5	BRS	L92	30	85 and (planar$6 or polish$5)	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:27			0
6	BRS	L99	30	92 and (dielectric or (tantalum adj1 oxide) or ("Ta.sub.2 O.sub.5"))	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:28			0
7	BRS	L106	5	99 and ("N.sub.2 O")	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:29			0
8	BRS	L113	30	99 and (anneal$5 or oxide or ("O.sub.2") or thermal or oxidation or heat or temperature)	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:30			0
9	BRS	L120	29	113 and (transistor or gate or source or drain)	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 10:31			0
10	BRS	L127	7554	barrier and ((threshold adj1 voltage) or ("V.sub.t"))	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 12:29			0
11	BRS	L134	369934	dielectric or (("Ta.sub.2 O.sub.5") or (high adj1 dielectric adj1 constant))	USPAT; US-PGP UB; EPO; JPO; DERWE NT; IBM_TD B	2003/04/28 12:32			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Erro rs
12	BRS	L141	3669	127 and 134	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:32			0
13	BRS	L148	1902	141 and ((silicon adj1 nitride) or ("Si.sub3 N.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:33			0
14	BRS	L155	1336	148 and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:34			0
15	BRS	L162	1216	155 and (open$5 or hol$3 or trench$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:36			0
16	BRS	L169	1209	162 and (transistor or gate or source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:37			0
17	BRS	L176	1209	169 and (("V.sub.t") or (threshold adj1 voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:38			0
18	BRS	L183	1187	176 and (planar$5 or oxide or ("N.sub.2 O"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:42			0
19	BRS	L190	738	183 and anneal$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:42			0
20	BRS	L204	1141	183 and (anneal$4 or thermal or oxidation or heat or temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 12:43			0